CLAIMS

1. An integrated circuit comprising:

an I/O pad of a first type made of a deposited conductor, wherein the I/O pad of the fist type is connected to a first point on the integrated circuit;

a strip of deposited conductor closely adjacent to the I/O pad of the fist type, wherein the strip of conductor is connected to a second point on the integrated circuit

2. The integrated circuit of claim 1, wherein the I/O pad of the first type is selected from a group consisting of a data I/O pad, a multi-level I/O pad and a power supply I/O pad.

3. The integrated circuit of claim 1, wherein the first point on the integrated circuit is further connected to a circuitry.

4. The integrated circuit of claim 1, wherein the first point on the integrated circuit is further connected to a power bus.

5. The integrated circuit of claim 1, wherein the second point on the integrated circuit is further connected to a circuitry.

6. The integrated circuit of claim 1, wherein the second point on the integrated circuit is further connected to a power bus.

7. The integrated circuit of claim 1, wherein the strip of conductor is connected to a third point on the integrated circuit.

8. The integrated circuit of claim 7, wherein the second and third points on the integrated circuit are connected to a circuitry.

9. The integrated circuit of claim 7, wherein the second and third points on the integrated circuit are connected to a power bus.

10. The integrated circuit of claim 1, further comprising an I/O pad of a second type made of a deposited conductor, wherein the I/O pad of the second type is connected to third point on the integrated circuit.

11. The integrated circuit of claim 10, wherein the I/O pad of the second type is selected from a group consisting of a data I/O pad, a multi-level I/O pad and a power supply I/O pad.

12. The integrated circuit of claim 10, wherein the third point on the integrated circuit is further connected to a circuitry.

13. The integrated circuit of claim 10, wherein the third point on the integrated circuit is further connected to a power bus.

14. The integrated circuit of claim 10, wherein the strip of conductor is connected to a fourth point on the integrated circuit.

15. The integrated circuit of claim 14, wherein the second, third and fourth points on the integrated circuit are connected to a circuitry.

16. The integrated circuit of claim 14, wherein the second, third and fourth points on the integrated circuit are connected to a power bus.

17. The integrated circuit of claim 1, wherein the I/O pad of the first type provides power to a core circuitry.

18. The integrated circuit of claims 4, 6, 9, 13 or 16, wherein the power bus is configured as an intersecting grid of a deposited conductor.

19. The integrated circuit of claim 18, wherein the integrated circuit is comprised of multiple metal layers, and wherein the I/O pad of the first type and the power bus are deposited on different layers.

20. The integrated circuit of claim 19, wherein the power bus exists at a lowest layer.

21. The integrated circuit of claim 19, wherein the power bus exists at a second to lowest layer.

22. An integrated circuit comprising:

a power supply I/O pad made of a deposited conductor;

a power bus connected to the power supply I/O pad;

a data I/O pad made of a deposited conductor;

circuitry connected to the data I/O pad; and

a strip of deposited conductor closely adjacent to the data I/O pad wherein the strip of conductor is connected to multiple points on the power bus.

23. The integrated circuit of claim 22, wherein the power bus provides power to a core circuitry.

24. The integrated circuit of claim 22, wherein the power bus is configured as an intersecting grid of a deposited conductor.

25. The integrated circuit of claim 22, wherein the integrated circuit is comprised of multiple metal layers, and wherein the power supply I/O pad and the power bus are deposited on different layers.

26. The integrated circuit of claim 25, wherein the power buss exists at the lowest layer.

27. The integrated circuit of claim 25, wherein the power bus exists at the second to the lowest layer.

28. An integrated circuit comprising:

a power supply I/O pad made of a deposited conductor;

a power bus connected to the power supply I/O pad;

a multi-level voltage I/O pad made of a deposited conductor;

circuitry connected to the multi-level voltage I/O pad; and

a strip of deposited conductor closely adjacent to the multi-level I/O pad wherein the strip of conductor is connected to multiple points on the power bus.

29. The integrated circuit of claim 28, wherein the power bus provides power to a core circuitry.

30. The integrated circuit of claim 28, wherein the power bus is configured as an intersecting grid of a deposited conductor.

31. The integrated circuit of claim 28, wherein the integrated circuit is comprised of multiple metal layers, and wherein the power supply I/O pad and the power bus are deposited on different layers.

32. The integrated circuit of claim 31, wherein the power buss exists at the lowest layer.

33. The integrated circuit of claim 31, wherein the power bus exists at the second to the lowest layer.

34. An integrated circuit comprising:

a positive power supply I/O pad made of a deposited conductor;

a positive power bus connected to the positive power supply I/O pad;

a negative power supply I/O pad made of a deposited conductor;

a negative power bus connected to the negative power supply I/O pad;

a data or multi-level voltage I/O pad made of a deposited conductor;

circuitry connected to the data or multi-level voltage I/O pad;

a first strip of deposited conductor closely adjacent to the data or multi-level I/O pad wherein the strip of conductor is connected to multiple points on the positive power bus; and

a second strip of deposited conductor closely adjacent to the data or multi-level I/O pad wherein the strip of conductor is connected to multiple points on the negative power bus.

35. The integrated circuit of claim 34, wherein the power buses provide positive and negative power to a core circuitry.

36. The integrated circuit of claim 34, wherein the power buses are configured as intersecting grids of a deposited conductor.

37. The integrated circuit of claim 34, wherein the integrated circuit is comprised of multiple metal layers, and wherein the positive and negative power buses are deposited on third and fourth layers, respectively.

38. The integrated circuit of claim 34, wherein the integrated circuit is comprised of multiple metal layers, and wherein the positive and negative power supply I/O pads are deposited on a first and second layer, respectively.

39. The integrated circuit of claim 38, wherein the first and second layers are the same layer.

40. The integrated circuit of claim 38, wherein the negative power bus exists at the lowest layer.

41. The integrated circuit of claim 38, wherein the positive power bus exists at the lowest layer.

42. The integrated circuit of claim 38, wherein the negative power bus exists at the second lowest layer.

43. The integrated circuit of claim 38, wherein the negative and positive power buses are further deposited on a fifth and sixth layer.

44. The integrated circuit of claim 38, wherein the positive power bus exists at the second lowest layer.

45. The integrated circuit of claim 44, wherein the negative power bus exists at the third lowest layer.

46. The integrated circuit of claim 44, wherein the positive power bus exists at the third lowest layer.

47. The integrated circuit of claim 44, wherein the negative power bus exists at the fourth lowest layer.

48. The integrated circuit of claim 44, wherein the positive power bus exists at the fourth lowest layer.